

## FEATURES

- ✧ High responsivity at 850 nm
- ✧ Low dark current
- ✧ Quick pulse response
- ✧ Hermetically sealed 3-pin metal case
- ✧ Active diameter 100  $\mu\text{m}$

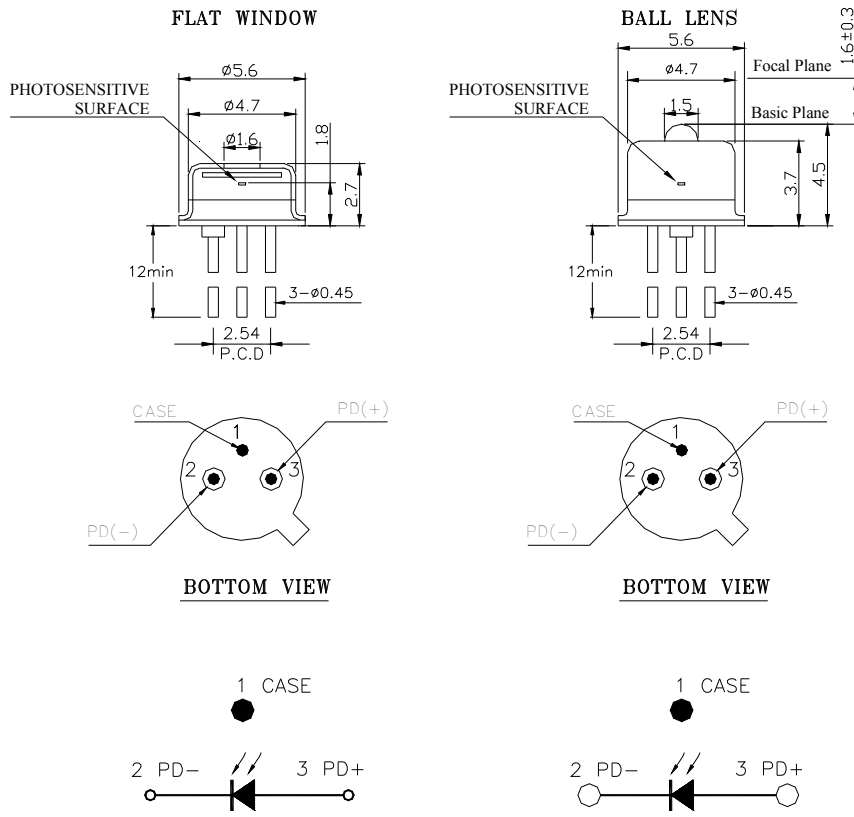
## DESCRIPTION

PD-8100 series InGaAs Photodiode are suited to receive the light at the wavelength 850 nm. With high reliability, PD-8100 series are the best choice for telecom and datacom application.

ELECTRICAL AND OPTICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ )						
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	Active Area			100		$\mu\text{m}$
	Detection Range			850		nm
R	Responsivity	$V_R=5\text{V}, \lambda=850\text{nm}$	0.45	0.50	-	A/W
$I_{\text{dark}}$	Dark Current	$V_R=5\text{V}$		0.1	0.7	nA
C	Capacitance	$V_R=5\text{V}$		0.4	0.7	pF
$T_r/T_f$	Rise/Fall Time	$V_R=5\text{V}, 10\sim 90\%$			0.15	ns
BW	Bandwidth	$V_R=5\text{V}$	2			GHz

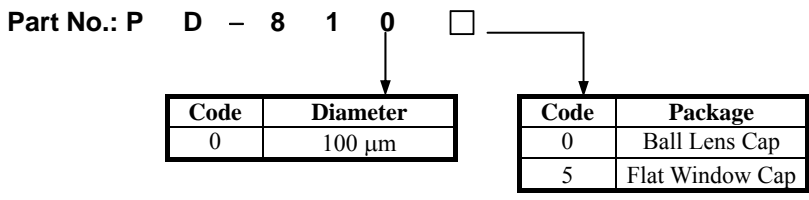
ABSOLUTE MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ )			
Symbol	Parameter	Ratings	Unit
$P_o$	Input Optical Power	2	mW
$V_{RD}$	Reverse Voltage	20	V
$I_{FD}$	Forward Current	2	mA
$T_{opr}$	Operating Temperature	-40~+85	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-40~+85	$^\circ\text{C}$

MECHANICAL DIMENSION (mm) and PIN ASSIGNMENT



**Note:** 1. Specifications subject to change without notice.  
 2. Other PIN assignment is available upon request.

ORDER INFORMATION



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Revision History

Version	Subject	Release Date
1.0	Initial datasheet	2002/9/1
2.0	Revise mechanical drawing	2009/4/9